2828 IFW

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OIPE JC139 JUL 0 2 2004 PATENT & TRADEMARK OFFICE

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July 2, 2004

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Commissioner for Patents
PO Box 1450
Alexandria, VA 22313-1450

Art Unit 2828

Re: U.S. Utility Patent Application
Application No. 09/604,097; Filed: June 27, 2000
For: **Semiconductor Light Emitting Device And Manufacturing Method Therefor**
Inventor: Yukio SHAKUDA
Our Ref: 2005.0020003

Sir:

Transmitted herewith for appropriate action are the following documents:

1. Seventh Supplemental Information Disclosure Statement;

2. Form PTO-1449 listing ONE-HUNDRED SEVENTY-THREE (173)documents (24 pages);

3. Copies of the ONE-HUNDRED SEVENTY-THREE (173) documents as listed on Form PTO-1449; and

4. One (1) return postcard.

It is respectfully requested that the attached postcard be stamped with the date of filing of these documents, and that it be returned to our courier. In the event that extensions of time are necessary to prevent abandonment of this patent application, then such extensions of time are hereby petitioned.

The U.S. Patent and Trademark Office is hereby authorized to charge any fee deficiency, or credit any overpayment, to our Deposit Account No. 19-0036.

Respectfully submitted,

STERNE, KESSLER, GOLDSTEIN & FOX P.L.L.C.

Thomas C. Fiala
Attorney for Applicant
Registration No. 43,610

TCF/mjg
Enclosures

OIPE JC139
JUL 0 2 2004
PATENT & TRADEMARK OFFICE

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:	Confirmation No.: 6648
Yukio SHAKUDA	Art Unit: 2828
Appl. No.: 09/604,097	Examiner: Tuan N. Nguyen
Filed: June 27, 2000	Atty. Docket: 2005.0020003
For: **Semiconductor Light Emitting Device And Manufacturing Method Therefor**	

Seventh Supplemental Information Disclosure Statement

Commissioner for Patents
PO Box 1450
Alexandria, VA 22313-1450

Sir:

Listed on accompanying Form PTO-1449 are documents that may be considered material to the examination of this application, in compliance with the duty of disclosure requirements of 37 C.F.R. §§ 1.56, 1.97 and 1.98. The numbering on this Seventh Supplemental Information Disclosure Statement is a continuation of the numbering in Applicant's Sixth Supplemental Information Disclosure Statement filed on November 14, 2003 in connection with the above-captioned application. This IDS is supplemental to an electronic IDS filed the same day. Any fee necessary for consideration of this Supplemental IDS has been authorized or otherwise submitted with the electronic IDS.

Where the publication date of a listed document does not provide a month of publication, the year of publication of the listed document is sufficiently earlier than the effective U.S. filing date and any foreign priority date so that the month of publication is not in issue. Applicant has listed publication dates on the attached PTO-1449 based on information presently available to the undersigned. However, the listed publication dates

should not be construed as an admission that the information was actually published on the date indicated.

Applicant reserves the right to establish the patentability of the claimed invention over any of the information provided herewith, and/or to prove that this information may not be prior art, and/or to prove that this information may not be enabling for the teachings purportedly offered.

This statement should not be construed as a representation that a search has been made, or that information more material to the examination of the present patent application does not exist. The Examiner is specifically requested not to rely solely on the material submitted herewith.

Applicant has checked the appropriate boxes below.

☐ 1. Statement under 37 C.F.R. 1.704(d). Each item of information contained in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart application and this communication was not received by any individual designated in 37 C.F.R. § 1.56(c) more than thirty days prior to the filing of this information disclosure statement.

☐ 2. Filing under 37 C.F.R. § 1.97(b). This Information Disclosure Statement is being filed within three months of the date of filing of a national application other than a continued prosecution application (CPA), OR within three months of the date of entry of the national stage as set forth in 37 C.F.R. § 1.491 in an international application, OR before the mailing date of a first Office Action on the merits OR

before the mailing of a first Office Action after the filing of a request for continued examination under 37 C.F.R. § 1.114. No statement or fee is required.

☒ 3. Filing under 37 C.F.R. § 1.97(c). This Information Disclosure Statement is being filed more than three months after the U.S. filing date AND after the mailing date of the first Office Action on the merits, but before the mailing date of a Final Rejection, or Notice of Allowance, or an action that otherwise closes prosecution in the application.

☐ a. Statement under 37 C.F.R. § 1.97(e)(1). I hereby state that each item of information contained in this Information Disclosure Statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Information Disclosure Statement. 37 C.F.R. § 1.97(e)(1).

☐ b. Statement under 37 C.F.R. § 1.97(e)(2). I hereby state that no item of information in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application and, to my knowledge after making reasonable inquiry, was known to any individual designated in 37 C.F.R. § 1.56(c) more than three months prior to the filing of this Information Disclosure Statement. 37 C.F.R. § 1.97(e)(2).

☒ ***c. Payment of the fee under 37 C.F.R. § 1.17(p) has already been made with the filing of an electronic IDS today.***

☐ 4. Filing under 37 C.F.R. § 1.97(d) This Information Disclosure Statement is being filed more than three months after the U.S. filing date and after the mailing date of a Final Rejection or Notice of Allowance, but before payment of the Issue Fee. Enclosed find our PTO-2038 Credit Card Payment Form in the amount of $_____ in payment of the fee under 37 C.F.R. § 1.17(p); in addition:

☐ a. Statement under 37 C.F.R. § 1.97(e)(1). I hereby state that each item of information contained in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Information Disclosure Statement. 37 C.F.R. § 1.97(e)(1).

☐ b. Statement under 37 C.F.R. § 1.97(e)(2). I hereby state that no item of information in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application and, to my knowledge after making reasonable inquiry, was known to any individual designated in 37 C.F.R. § 1.56(c) more than three months prior to the filing of this Information Disclosure Statement. 37 C.F.R. § 1.97(e)(2).

☐ 5. The document(s) was/were cited in a search report by a foreign patent office in a counterpart foreign application. Submission of an English language version of the search report that indicates the degree of relevance found by the foreign office is provided in satisfaction of the requirement for a concise explanation of relevance. 1138 OG 37, 38.

☒ 6. A concise explanation of the relevance of the non-English language document(s) appears below:

Documents AC47, AD47, AA48, AB48, AC48, AD48, AA49, AB49, AC49, AD49, and AA50 are in a foreign language. For an explanation of relevance, an English-language abstract is attached as the first page of each document.

Documents AK65, AE66, and AF66 are in a foreign language. These documents were apparently produced by Nichia Corporation during litigation with Rohm Company, Ltd. involving U.S. Patent Nos. 6,084,899 and U.S. Patent No. 6,115,399. The present application claims priority to each of these U.S. Patents.

☒ 7. Copies of the documents are submitted herewith.

☐ 8. Copies of the documents were cited by or submitted to the Office in an IDS that complies with 37 C.F.R. § 1.98(a)-(c) in Application No._____, filed _____, which is relied upon for an earlier filing date under 35 U.S.C. § 120. Thus, copies of these documents are not attached. 37 C.F.R. § 1.98(d).

☐ 9. No copies of U.S. patents and patent application publications cited on the attached Form PTO-1449 are submitted in accordance with 1276 OG 55 because this application was filed after June 30, 2003.

☐ 10. It is expected that the examiner will review the prosecution and cited art in the parent application nos. _____ in accordance with MPEP 2001.06(b), and indicate in the next communication from the office that the art cited in the earlier prosecution history has been reviewed in connection with the present application.

It is respectfully requested that the Examiner initial and return a copy of the enclosed PTO-1449, and indicate in the official file wrapper of this patent application that the documents have been considered.

The U.S. Patent and Trademark Office is hereby authorized to charge any fee deficiency, or credit any overpayment, to our Deposit Account No. 19-0036.

Respectfully submitted,

STERNE, KESSLER, GOLDSTEIN & FOX P.L.L.C.

Thomas C. Fiala
Attorney for Applicant
Registration No. 43,610

Date: 7/2/09

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OIPE JC139 JUL 0 2 2004 PATENT & TRADEMARK OFFICE

FORM PTO-1449

SEVENTH SUPPLEMENTAL
INFORMATION DISCLOSURE STATEMENT

ATTY. DOCKET NO.	APPLICATION NO.
2005.0020003	09/604,097
INVENTOR	
Yukio SHAKUDA	
FILING DATE	ART UNIT
June 27, 2000	2828

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOC. REF.	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION
	AA						N/A
	AB						N/A
	AC46	1,325,582	12/1993	CA			N/A
	AD46	0 356 059 A2	02/1990	EP			N/A

OTHER (Including Author, Title, Date, Pertinent Pages, etc.)

	AE	
	AF	
	AG	
	AH	
	AI	
	AJ	
	AK47	*Response of Nichia America Corporation To Amended Complaint of Rohm Co., Ltd. And Notice of Investigation*, with Exhibits D-H, 120 Pages, Dated February 13, 2001 In the Matter of Certain Semiconductor Light Emitting Devices, Components Thereof, and Products Containing Same, Investigation No. 337-TA-444 before the U.S. International Trade Commission.

EXAMINER	DATE CONSIDERED

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

OIPE JC139
JUL 0 2 2004
PATENT & TRADEMARK OFFICE

FORM PTO-1449

SEVENTH SUPPLEMENTAL
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FILING DATE	ART UNIT
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FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOC. REF.	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION
	AA47	778,383	07/1957	GB			N/A
	AB47	1,011,979	12/1965	GB			N/A
	AC47	2-74088 A	03/1990	JP			Abstract Enclosed
	AD47	2-111016 A	04/1990	JP			Abstract Enclosed

OTHER (Including Author, Title, Date, Pertinent Pages, etc.)

	AE48	*Respondent Nichia Corporation's Objections and Responses To Complainant Rohm Co., Ltd.'s Fourth Set of Interrogatories Nos. 110-120*, 20 Pages, Dated March 28, 2001 In the Matter of Certain Semiconductor Light Emitting Devices, Components Thereof, and Products Containing Same, Investigation No. 337-TA-444 before the U.S. International Trade Commission.
	AF48	*Order No. 6: Denying Motion of Respondents Nichia Corporation and Nichia America Corporation for Sanctions for Abuse of Commission Process, and to Show Cause Why Rohm Co. Ltd. Has Not Violated Commission Rule 210.4(c)*, 12 Pages, Dated June 27, 2001 In the Matter of Certain Semiconductor Light Emitting Devices, Components Thereof, and Products Containing Same, Investigation No. 337-TA-444 before the U.S. International Trade Commission.
	AG48	*Response and Counterclaim of Nichia Corporation and Nichia America Corporation*, 27 Pages, Dated November 9, 2001, in Rohm Co., Ltd. v. Nichia Corporation and Nichia America Corporation v. Rohm Co., Ltd., and Cree, Inc., Civil Action No. 00-CV-6379, U.S. District Court for the Eastern District of Pennsylvania.
	AH48	*Notice*, 4 Pages, Dated March 8, 2002 In the Matter of Certain Semiconductor Light Emitting Devices, Components Thereof, and Products Containing Same, Investigation No. 337-TA-444 before the U.S. International Trade Commission.
	AI48	*Nichia's Expedited Motion to Declare Rohm's Certificates of Correction Ineffective for this Action*, 3 Pages, Dated June 26, 2003, in Rohm Co., Ltd. v. Nichia Corporation and Nichia America Corporation v. Rohm Co., Ltd., Civil Action No. 00-CV-6379, U.S. District Court for the Eastern District of Pennsylvania.
	AJ48	*Memorandum in Support of Nichia's Expedited Motion to Declare Rohm's Certificates of Correction Ineffective for this Action*, with Exhibits A-H, 61 Pages, Dated June 26, 2003, in Rohm Co., Ltd. v. Nichia Corporation and Nichia America Corporation v. Rohm Co., Ltd., Civil Action No. 00-CV-6379, U.S. District Court for the Eastern District of Pennsylvania.
	AK48	*Nichia Corporation's Objections and Responses to Rohm's Second Set of Interrogatories (Nos. 9-15)*, 16 Pages, Dated July 10, 2003, in Rohm Co., Ltd. v. Nichia Corporation and Nichia America Corporation v. Rohm Co., Ltd., Civil Action No. 00-CV-6379, U.S. District Court for the Eastern District of Pennsylvania.

EXAMINER	DATE CONSIDERED

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FORM PTO-1449

SEVENTH SUPPLEMENTAL
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ATTY. DOCKET NO.	APPLICATION NO.
2005.0020003	09/604,097
INVENTOR	
Yukio SHAKUDA	
FILING DATE	ART UNIT
June 27, 2000	2828

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOC. REF.	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION
	AA48	3-85785 A	04/1991	JP			Abstract Enclosed
	AB48	3-289187 A	12/1991	JP			Abstract Enclosed
	AC48	4-111375 A	04/1992	JP			Abstract Enclosed
	AD48	4-130692 A	05/1992	JP			Abstract Enclosed

OTHER (Including Author, Title, Date, Pertinent Pages, etc.)

	AE49	*Nichia's Brief in Opposition to Rohm's Motion for Leave to File a Supplemental Pleading and in Support of Nichia's Expedited Motion to Declare Rohm's Certificates of Correction Ineffective for this Action*, 7 Pages, Dated July 22, 2003, in Rohm Co., Ltd. v. Nichia Corporation and Nichia America Corporation v. Rohm Co., Ltd., Civil Action No. 00-CV-6379, U.S. District Court for the Eastern District of Pennsylvania.
	AF49	*Nichia's Motion to Strike the '899 Patent from the Case*, 3 Pages, Dated September 11, 2003, in Rohm Co., Ltd. v. Nichia Corporation and Nichia America Corporation v. Rohm Co., Ltd., Civil Action No. 00-CV-6379, U.S. District Court for the Eastern District of Pennsylvania.
	AG49	*Memorandum in Support of Nichia's Motion to Strike the '899 Patent from the Case*, with Exhibits 1-2, 63 Pages, Dated September 11, 2003, in Rohm Co., Ltd. v. Nichia Corporation and Nichia America Corporation v. Rohm Co., Ltd., Civil Action No. 00-CV-6379, U.S. District Court for the Eastern District of Pennsylvania.
	AH49	*Brief of Rohm Co., Ltd. in Opposition to Nichia's Motion to Strike the '899 Patent from the Case*, with Exhibits 1-4, 29 Pages, Dated September 25, 2003, in Rohm Co., Ltd. v. Nichia Corporation and Nichia America Corporation v. Rohm Co., Ltd., Civil Action No. 00-CV-6379, U.S. District Court for the Eastern District of Pennsylvania.
	AI49	*Nichia's Opposition to Rohm's Motion to Compel*, with Exhibit 1, 48 Pages, Dated September 26, 2003, in Rohm Co., Ltd. v. Nichia Corporation and Nichia America Corporation v. Rohm Co., Ltd., Civil Action No. 00-CV-6379, U.S. District Court for the Eastern District of Pennsylvania.
	AJ49	*Reply Memorandum in Support of Nichia's Motion to Strike the '899 Patent from the Case*, 10 Pages, Dated October 2, 2003, in Rohm Co., Ltd. v. Nichia Corporation and Nichia America Corporation v. Rohm Co., Ltd., Civil Action No. 00-CV-6379, U.S. District Court for the Eastern District of Pennsylvania.
	AK49	*Nichia's Emergency Motion to Compel the Deposition of Alleged Sole Inventor Yukio Shakuda to Proceed on January 30, 2004 and to Compel Shakuda to Review and Bring Documents Supporting His Alleged Inventorship*, with Proposed Order, 7 Pages, Dated October 8, 2003, in Rohm Co., Ltd. v. Nichia Corporation and Nichia America Corporation v. Rohm Co., Ltd., Civil Action No. 00-CV-6379, U.S. District Court for the Eastern District of Pennsylvania.

EXAMINER	DATE CONSIDERED

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

OIPE JC#39
JUL 0 2 2004
PATENT & TRADEMARK OFFICE

FORM PTO-1449

SEVENTH SUPPLEMENTAL
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ATTY. DOCKET NO.	APPLICATION NO.
2005.0020003	09/604,097
INVENTOR	
Yukio SHAKUDA	
FILING DATE	ART UNIT
June 27, 2000	2828

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOC. REF.	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION
	AA49	4-144296 A	05/1992	JP			Abstract Enclosed
	AB49	4-309281 A	10/1992	JP			Abstract Enclosed
	AC49	5-160504 A	06/1993	JP			Abstract Enclosed
	AD49	2908815 B2	04/1999	JP			Abstract Enclosed

OTHER (Including Author, Title, Date, Pertinent Pages, etc.)

	AE50	*Brief in Support of Nichia's Emergency Motion to Compel the Deposition of Alleged Sole Inventor Yukio Shakuda to Proceed on January 30, 2004 and to Compel Shakuda to Review and Bring Documents Supporting His Alleged Inventorship*, with Exhibits A-D, 33 Pages, Dated October 8, 2003, in Rohm Co., Ltd. v. Nichia Corporation and Nichia America Corporation v. Rohm Co., Ltd., Civil Action No. 00-CV-6379, U.S. District Court for the Eastern District of Pennsylvania.
	AF50	*Clarification to Nichia's Motion to Strike the '899 Patent from the Case and Nichia's Response to Rohm's Motion to Compel*, with Exhibits A-C, 16 Pages, Dated October 14, 2003, in Rohm Co., Ltd. v. Nichia Corporation and Nichia America Corporation v. Rohm Co., Ltd., Civil Action No. 00-CV-6379, U.S. District Court for the Eastern District of Pennsylvania.
	AG50	*Reply Memorandum in Support of Nichia's Motion Compel*, with Exhibit 1, 24 Pages, Dated November 3, 2003, in Rohm Co., Ltd. v. Nichia Corporation and Nichia America Corporation v. Rohm Co., Ltd., Civil Action No. 00-CV-6379, U.S. District Court for the Eastern District of Pennsylvania.
	AH50	*Reply Brief in Support of Nichia's Emergency Motion to Compel the Deposition of Alleged Sole Inventor Yukio Shakuda to Proceed on January 30, 2004 and to Compel Shakuda to Review and Bring Documents Supporting His Alleged Inventorship*, with Exhibits A-D, 29 Pages, Dated December 4, 2003, in Rohm Co., Ltd. v. Nichia Corporation and Nichia America Corporation v. Rohm Co., Ltd., Civil Action No. 00-CV-6379, U.S. District Court for the Eastern District of Pennsylvania.
	AI50	*Motion and Stipulation of Voluntary Dismissal with Prejudice Pursuant to Federal Rule of Civil Procedure 41(a)(2)*, 2 Pages, Dated February 12, 2004, in Rohm Co., Ltd. v. Nichia Corporation and Nichia America Corporation, Civil Action No. 00-CV-6379, U.S. District Court for the Eastern District of Pennsylvania.
	AJ50	"Hole Compensation Mechanism of p-Type GaN Films," 9 pages.
	AK50	"Shallow Impurity Passivation by Atomic Hydrogen," 14 pages.

EXAMINER	DATE CONSIDERED

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

OIPE JC13 JUL 0 2 2004 PATENT & TRADEMARK OFFICE

FORM PTO-1449

SEVENTH SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

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2005.0020003	09/604,097
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FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOC. REF.	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION
	AA50	6-219892 A	08/1994	JP			Abstract Enclosed
	AB50						N/A
	AC50						N/A
	AD50						N/A

OTHER (Including Author, Title, Date, Pertinent Pages, etc.)

	AE51	Lockwood, H.F. *et al.*, "An Efficient Large Optical Cavity Injection Laser," *Applied Physics Letters*, Vol. 17, No. 11, pp. 499-502 (December 1, 1970).
	AF51	Thompson, G.H.B. and Kirkby, P.A., "(GaAl)As Lasers With a Heterostructure for Optical Confinement and Additional Heterojunctions for Extreme Carrier Confinement," *IEEE Journal of Quantum Electronics*, Vol. QE-9, No. 2, pp. 311-318 (February 1973).
	AG51	Maruska, H.P. *et al.*, "Microstructural Observations on Gallium Nitride Light-Emitting Diodes," *J. Electrochem. Soc.: Solid-State Science and Technology*, pp. 1202-1207 (September 1974).
	AH51	Robinson, R.J. and Kun, Z.K., "*p-n* junction zinc sulfo-selenide and zinc selenide light-emitting diodes," *Applied Physics Letters*, Vol. 27, No. 2, American Institute of Physics, pp. 74-76 (July 15, 1975).
	AI51	Pearton, S.J. *et al.*, "Hydrogen passivation of shallow level impurities and deep level defects in GaAs," *Inst. Phys. Conf. Ser. No. 83: Chapter 5*, (Paper presented at Int. Symp. GaAs and Related Compounds, Las Vegas, Nevada), pp. 289-294, IOP Publishing Ltd. (1986).
	AJ51	Thompson, G.H.B. *et al.*, "Narrow-beam five-layer (GaAl)As/GaAs heterostructure lasers with low threshold and high peak power," *Journal of Applied Physics*, Vol. 47, No. 4, American Institute of Physics, pp. 1501-1505 (April 1976).
	AK51	Chinone, N. *et al.*, "Highly efficient (GaAl)As buried-heterostructure lasers with buried optical guide," *Applied Physics Letters*, Vol. 35, No. 7, pp. 513-516 (October 1, 1979).

EXAMINER	DATE CONSIDERED

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	AA51						N/A
	AB51						N/A
	AC51						N/A
	AD51						N/A

OTHER (Including Author, Title, Date, Pertinent Pages, etc.)

	AE52	Thompson, G.H.B., *Physics of Semiconductor Laser Devices*, John Wiley & Sons, pp. 262-268 (1980).
	AF52	Botez, D., "cw high-power single-mode operation of constricted double-heterojunction AlGaAs lasers with a large optical cavity," *Applied Physics Letters*, Vol. 36, No. 3, American Institute of Physics, pp. 190-192 (February 1, 1980).
	AG52	Mito, I. *et al.*, "InGaAsP Planar Buried Heterostructure Laser Diode (PBH-LD) with Very Low Threshold Current," *Electronics Letters*, Vol. 18, No. 1, pp. 2-3 (January 7, 1982).
	AH52	Kun, Z.K., "The variation of residual impurities in ZnSe crystals used in light-emitting diode fabrications," *Journal of Applied Physics*, Vol. 53, No. 2, American Institute of Physics, pp. 1248-1250 (February 1982).
	AI52	Magnea, N. *et al.*, "SEM and Photoluminescence Study of Li Segregation in Annealed Zinc Telluride," *Solid State Communications*, Vol. 29, No. 1, Pergamon Press Ltd., pp. 35-38 (1979).
	AJ52	Dean, P.J. *et al.*, "Ionization energy of the shallow nitrogen acceptor in zinc selenide," *Physical Review B*, Vol. 27, No. 4, The American Physical Society, pp. 2419-2428 (February 15, 1983).
	AK52	Khan, M.A. *et al.*, "Properties and ion implantation of $Al_xGa_{1-x}N$ epitaxial single crystal films prepared by low pressure metalorganic chemical vapor deposition," *Applied Physics Letters*, Vol. 43, No. 5, American Institute of Physics, pp. 492-494 (September 1, 1983).

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	AC52						N/A
	AD52						N/A

OTHER (Including Author, Title, Date, Pertinent Pages, etc.)

	AE53	Sah, C.-T. *et al.*, "Study of the atomic models of three donor-like traps on oxidized silicon with aluminum gate from their processing dependencies," *Journal of Applied Physics*, Vol. 54, No. 10, American Institute of Physics, pp. 5864-5879 (October 1983).
	AF53	Pankove, J.I. *et al.*, "Neutralization of Shallow Acceptor Levels in Silicon by Atomic Hydrogen," *Physical Review Letters*, Vol. 51, No. 24, The American Physical Society, pp. 2224-2225 (December 12, 1983).
	AG53	Hashimoto, M., "Effects of Hydrogen in an Ambient on the Crystal Growth of GaN Using $Ga(CH_3)_3$ and NH_3," *Journal of Crystal Growth*, Vol. 68, Elsevier, Science Publishers B.V., pp. 163-168 (1984).
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	AI53	Gowar, J., *Optical Communication Systems*, Second Edition, Prentice Hall, p. 414 (1984).
	AJ53	Pankove, J.I. *et al.*, "Hole-mediated chemisorption of atomic hydrogen in silicon," *Applied Physics Letters*, Vol. 47, No. 7, American Institute of Physics, pp. 748-750 (October 1, 1985).
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FORM PTO-1449

SEVENTH SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

ATTY. DOCKET NO.	APPLICATION NO.
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INVENTOR	
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	AA53						N/A
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OTHER (Including Author, Title, Date, Pertinent Pages, etc.)

	AE54	Agrawal, G.P. and Dutta, N.K., *Long-Wavelength Semiconductor Lasers*, Van Nostrand Reinhold Company, p. 194 (1986).
	AF54	Mawst, L.J. *et al.*, "MOCVD of III-V Compound Epitaxial Layers," *Semiconductor International*, pp. 61-63 (November 1986).
	AG54	Pajot, B. *et al.*, "Spectroscopic evidence for the hydrogen passivation of zinc acceptors in gallium arsenide," *Semiconductor Science Technology 2*, IOP Publishing Ltd., pp. 305-307 (1987).
	AH54	Koide, Y. *et al.*, "Energy band-gap bowing parameter in an $AL_xGA_{1-x}N$ alloy," *Journal of Applied Physics*, Vol. 61, No. 9, American Institute of Physics, pp. 4540-4543 (May 1, 1987).
	AI54	Yoo, T.-K. *et al.*, "Surface-Emitting AlGaAs/GaAs DH LED with Buried-Window Cylindrical Lens," pp. L2357-L2360 (December 1988).
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	AA54						N/A
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	AD54						N/A

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	AE55	Moustakas, T.D. and Molnar, R.J., "Growth and Doping of GaN Films by ECR-Assisted MBE," *Mat. Res. Soc. Symp. Proc.*, Vol. 281, Materials Research Society, pp. 753, 755, 757, 759, 761 and 763 (1993).
	AF55	*Transmission Mode 3rd Gen. Photocathode Configuration*, 1 page.
	AG55	Van Vechten, J.A. *et al.*, "Defeating Compensation in Wide Gap Semiconductors by Growing in H that is Removed by Low Temperature De-Ionizing Radiation," *Japanese Journal of Applied Physics*, Vol. 31, Part 1, No. 11, pp. 3662-3663 (November 1992).
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	AE56	"APA, AT&T In Laser Technology Pact," *Electronic News*, p. 50, February 7, 1994).
	AF56	"Blue-Green-Laser Pact Signed by APA Optics and AT&T," *BusinessWorld Briefs*, 1 page (March 1994).
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	AJ56	Thompson, G.H.B., *Physics of Semiconductor Laser Devices*, John Wiley & Sons, pp. 156, 157, 262, 262-265 (1980).
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	AE57	Einspruch, N.G. and Frensley, W.R. (eds)., *Heterostructures and Quantum Devices*, Academic Press, pp. 220-222 (1994).
	AF57	Verdeyen, J. T., *Laser Electronics*, Second Edition, Prentice Hall, pp. 389-392 (1989).
	AG57	Osamura, K. *et al.*, "Fundamental Absorption Edge In GaN, InN and Their Alloys," *Solid State Communications*, Vol. 11, No. 5, Pergamon Press, pp. 617-621 (1972).
	AH57	Akasaki, I. and Amano, H., "MOVPE Growth of High Quality $Al_xGa_{1-x}N/Ga_yIN_{1-y}N$ ($x \geq 0$, $y \leq 1$) Heterostructures for Short Wavelength Light Emitter," *Materials Research Society Symposium Proceedings*, Vol. 339, pp. 443-452 (1994).
	AI57	Amano, H. *et al.*, "Room-temperature violet stimulated emission from optically pumped AlGaN/GaInN double heterostructure," *Applied Physics Letters*, Vol. 64, No. 11, American Institute of Physics, pp. 1377-1379 (March 14, 1994).
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OTHER (Including Author, Title, Date, Pertinent Pages, etc.)

	AE58	Kamata, N. *et al.*, "Separation of non-radiative and below-gap emission lifetimes in a heavily Si-doped GaAs/AlGaAs quantum well," *Journal of Luminescence 48 & 49*, Elsevier Science Publishers B.V., pp. 763-767 (1991).
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	AI58	Streifer, W. *et al.*, "An Analytic Study of (GaAl)As Gain Guided Lasers at Threshold," *IEEE Journal of Quantum Electronics*, Vol. QE-18, No. 5, IEEE, pp. 856-864 (May 1982).
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OTHER (Including Author, Title, Date, Pertinent Pages, etc.)

	AE59	Mataki, H. *et al.*, "Mass production of AlGaAs laser diodes using MBE," *SPIE Proceedings: Fiber Optic Materials and Components*, The International Society for Optical Engineering, Vol. 2290, pp. 321-330 (July 28-29, 1984).
	AF59	Sakiyama, H. and Takuma, H., "AlGaAs Laser Diodes by the Molecular Beam Epitaxy Method," *Journal of Electronic Engineering*, Vol. 26, No. 270, Dempa Publications, Inc., pp. 40-42 (May 1989).
	AG59	Smith, F.W. *et al.*, "New MBE Buffer Used to Eliminate Backgating in GAAs MESFET's," *IEEE Electron Device Letters*, Vol. 9, No. 2, IEEE, pp. 77-80 (February 1988).
	AH59	Tsou, Y. and Garmire, E.M., "Improving InAs Double Heterostructure Lasers with Better Confinement," *IEEE Journal of Quantum Electronics*, Vol. 28, No. 5, pp. 1261-1268 (May 1992).
	AI59	Kawanaka, S. *et al.*, "Strained Single Quantum Well AlGaInP Laser Diodes with an Asymmetric Waveguiding Layer," *Extended Abstracts of the 1992 International Conference on Solid State Devices and Materials, Tsukuba*, pp. 240-242 (August 26-28, 1992).
	AJ59	Itaya, K. *et al.*, "Highly Reliable 100mW Operation of Broad Area InGaAlP Visible Light Laser Diodes," *Electronics Letters*, Vol. 27, No. 24, pp. 2257-2259 (November 21, 1991).
	AK59	Botez, D., "The Effect of Carried-Induced Index Depressions on Fundamental-Transverse-Mode Characteristics in DH Laser Structures," *RCA Review*, Vol. 45, No. 1, RCA Laboratories, pp. 23-32 (March 1984).

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	INVENTOR Yukio SHAKUDA	
	FILING DATE June 27, 2000	ART UNIT 2828

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OTHER (Including Author, Title, Date, Pertinent Pages, etc.)

	AE60	Kazi, K. and Jain, F.C., "Modal Analysis of IncGaAsP-InP, GaAs/AlGaAs-GaAs, and InGaAsP/AlGaAs-GaAs MIS Heterostructure Lasers," *International Journal of Infrared and Millimeter Waves*, Vol. 7, No. 6, Plenum Publishing Corporation, pp. 891-907 (June 1986).
	AF60	Murata, H. *et al.*, "Low Threshold Current Density of 620 nm Band MQW-SCH AlGaInP Semiconductor Lasers With Mg Doped AlInP Cladding Layer," *Electronics Letters*, Vol. 27, No. 17, IEE, pp. 1569-1571 (August 15, 1991).
	AG60	Shah, P. and Mitin, V., "Threshold Characteristics of Blue to Ultraviolet Light Emitting Semiconductor Lasers Based on the AlGaN Material System," IEEE, pp. 160-169 (1995).
	AH60	Kolbas, R.M. and Krishnankutty, S., "Optoelectronic Properties of GaN, AlGaN and AlGaN-GaN Quantum Well Heterostructures," pp. 19-20.
	AI60	Akasaki, I. and Amano, H., "UV/Blue Light Emitting AlGaN/GaN Heterostructures," pp. 14-15.
	AJ60	Benchimol, J.L. *et al.*, "Growth and modelling of InAsPSb. InAs double heterostructures," *Inst. Phys. Conf. Ser. No. 83: Chapter 7 - Paper presented at Int. Symp. GaAs and Related Compounds, Las Vegas, Nevada*, IOP Publishing Ltd., pp. 385-390 (September 28 - October 1, 1986).
	AK60	Suemune, I., "Theoretical Estimation of Leakage Current in II-VI Heterostructure Lasers," *Japanese Jounral of Applied Physics*, Vol. 31, Part 2, No. 2A, pp. L95-L98 (February 1, 1992).

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	INVENTOR Yukio SHAKUDA	
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OTHER (Including Author, Title, Date, Pertinent Pages, etc.)

	AE61	Watanabe, M.O. and Ohba, Y., "Interface properties for GaAs/InGaAlP heterojunctions by the capacitance-voltage profiling technique," *Applied Physics Letters*, Vol. 50, No. 14, American Institute of Physics, pp. 906-908 (April 6, 1987).
	AF61	Yablonovitch, E. and Kane, E.O., "Reduction of Lasing Threshold Current Density by the Lowering of Valence Band Effective Mass," *Journal of Lightwave Technology*, Vol. LT-4, No. 5, IEEE, pp. 504-506 (May 1986).
	AG61	Mori, K. *et al.*, "Band Discontinuity Reduction of i-GaInAsP/p-InP for Improving 1.55μm GaInAsP/InP Surface Emitting Laser Performances," *Conference Proceedings - Sixth International Conference on Indium Phosphide and Related* Materials, IEEE, pp. 311-314 (March 27-31, 1994).
	AH61	Ohki, Y. *et al.*, "Fabrication and properties of a practical blue-emitting GaN m-i-s diode," *Inst. Phys. Conf. Ser. No. 63: Chapter 10 - Paper presented at Int. Symp. GaAs and Related Compounds, Japan*, The Institute of Physics, pp. 479-484 (1981).
	AI61	Amano, H. *et al.*, "Metalorganic vapor phase epitaxial growth of a high quality GaN film using an AlN buffer layer," *Applied Physics Letters*, Vol. 48, No. 5, American Institute of Physics, pp. 353-355 (February 3, 1986).
	AJ61	Haase, M.A. *et al.*, "Blue-green laser diodes," *Applied Physics Letters*, Vol. 59, No. 11, American Institute of Physics, pp. 1272-1274 (September 9, 1991).
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	AE62	Khan, M.A. *et al.*, "Vertical-cavity, room-temperature stimulated emission from photopumped GaN films deposited over sapphire substrates using low-pressure metalorganic chemical vapor deposition," *Applied Physics Letters*, Vol. 58, No. 14, American Institute of Physics, pp. 1515-1517 (April 8, 1991).
	AF62	Kressel, H. and Butler, J.K. (eds.), *Semiconductor Lasers and Heterojunction LEDs*, Academic Press, pp. 137-141, 205-207, 222-235, 264-271, 280-287 and 456-461 (1977).
	AG62	Ohtsu, M., *Highly Coherent Semiconductor Lasers*, Artech House, Inc., pp. 15-21 (1992).
	AH62	Botez, D. and Connolly, J.C., "Terraced-heterostructure large-optical-cavity AlGaAs diode laser: A new type of high-power cw single-mode device," *Applied Physics Letters*, Vol. 41, No. 4, American Institute of Physics, pp. 310-312 (August 15, 1982).
	AI62	Henderson, G.N. *et al.*, "Optical transitions to above-barrier quasibound states in asymmetric semiconductor heterostructures," *Applied Physics Letters*, Vol. 62, No. 12, American Institute of Physics, pp. 1432-1434 (March 22, 1993).
	AJ62	Akasaki, I. and Amano, H., "Room Temperature Ultraviolet/Blue Light Emitting Devices Based on AlGaN/GaN Multi-Layered Structure," *Extended Abstracts of the 1992 International Conference on Solid State Devices and Materials, Tsukuba*, pp. 327-329 (1992).
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	AE63	Amano, H. *et al.*, "Room-Temperature Low-Threshold Surface-Stimulated Emission by Optical Pumping from $AL_{0.1}Ga_{0.9}N$/GaN Double Heterostructure," *Japanese Journal of Applied Physics*, Vol. 32, Part 2, No. 7B, pp. L1000-L1002 (July 15, 1993).
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	AG63	Evans, G.A. *et al.*, "Observations and Consequences of Nonuniform Aluminum Concentration in the Channel Regions of AlGaAs Channeled-Substrate-Planer Lasers," *IEEE Journal of Quantum Electronics*, Vol. QE-23, No. 11, IEEE, pp. 1900-1908 (November 11, 1987).
	AH63	Iyer, S.V. *et al.*, "Modeling of distortions in optical characteristics of semiconductor lasers due to noise in MBE growth temperature measurement," *SPIE Proceedings - Physics and Simulation of Optoelectronic Devices II*, Vol. 2146, The International Society for Optical Engineering, pp. 148-159 (January 24-26, 1994).
	AI63	Jennings, A. *et al.*, "Asymmetric Fabry-Perot Device Arrays with Low Insertion Loss and High Uniformity," *IEEE Photonics Technology Letters*, Vol. 4, No. 8, IEEE, pp. 858-860 (August 1992).
	AJ63	Koike, M. *et al.*, "Light-Emitting Devices Based on Gallium Nitride and Related Compound Semiconductors," *Materials Research Society Symposium Proceedings*, Vol. 395, Materials Research Society, pp. 889-895 (November 27 - December 1, 1995).
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	AE64	Figueroa, L. *et al.*, "High Power Semiconductor Lasers," *SPIE Proceedings - Progress in Laser Diodes*, Vol. 723, The International Society for Optical Engineering, pp. 2-24 (September 25-26, 1986).
	AF64	Garmire, E. *et al.*, "Longitudinal mode control in GaAs lasers using a three-mirror active-passive cavity," pp. 106-108, Reprinted from *Applied Physics Letters*, Vol. 39, No. 10, American Institute of Physics, pp. 789-791 (November 15, 1981).
	AG64	Reinhart, F.K. *et al.*, "GaAs-$Al_xGa_{1-x}As$ injection lasers with distributed Bragg reflectors," pp. 173-175, Reprinted from *Applied Physics Letters*, Vol. 27, No. 1, American Institute of Physics, pp. 45-48 (July 1, 1975).
	AH64	Kressel, H. *et al.*, "Low-Threshold $AL_xGA_{1-x}As$ Visible and IR-Light-Emitting Diode Lasers," pp. 285-291, Reprinted from *IEEE Journal of Quantum Electronics*, Vol. QE-6, No. 6, IEEE, pp. 278-284 (June 1970).
	AI64	Ikeda, M. *et al.*, "Room-temperature continuous-wave operation of an AlGaInP double heterostructure laser grown by atmospheric pressure metalorganic chemical vapor deposition," pp. 295-296, Reprinted from *Applied Physics Letters*, Vol. 47, No. 10, American Institute of Physics, pp. 1027-1028 (November 15, 1985).
	AJ64	Morkoç, H. *Nitride Semiconductors and Devices*, Springer, pp. 26-31 and 57-66.
	AK64	Khan, M.A. *et al.*, "Growth of high optical and electrical quality GaN layers using low-pressure metalorganic vapor deposition," *Applied Physics Letters*, Vol. 58, No. 5, American Institute of Physics, pp. 526-527 (February 4, 1991).

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FORM PTO-1449 SEVENTH SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT	ATTY. DOCKET NO. 2005.0020003	APPLICATION NO. 09/604,097
	INVENTOR Yukio SHAKUDA	
	FILING DATE June 27, 2000	ART UNIT 2828

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOC. REF.	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION
	AA						N/A
	AB						N/A
	AC						N/A
	AD						N/A

OTHER (Including Author, Title, Date, Pertinent Pages, etc.)

	AE65	Akasaki, I. and Amano, H., "Conductivity Control of AlGaN, Fabrication of AlGaN/GaN Multi-Heterostructure and Their Application to UV/Blue Light Emitting Devices," *Materials Research Society Symposium Proceedings*, Vol. 242, Materials Research Society, pp. 383-394 (1992).
	AF65	Sturge, M.D. (ed.), *Journal of Luminescence: An Interdisciplinary Journal of Research on Excited State Processes in Condensed Matter*, Vols. 48 and 49, Part II, North-Holland, Cover page (1991).
	AG65	*Japanese Journal of Applied Physics*, Vol. 29, No. 4, Part 2 Letters, Table of Contents (April 1990).
	AH65	Christou, A. and Rupprecht, H.S. (eds.), *Proceedings of the Fourteenth International Symposium on Gallium Arsenide and Related Compounds held in Heraklion, Crete*, IOP Publishing Ltd., Cover page (September 28 - October 1, 1987).
	AI65	*Journal of Electronic Materials*, Vol. 19, No. 7, IEEE, pp. 17-18 (July 1990).
	AJ65	*CLEO®'94 Summaries of papers presented at the Conference on Lasers and Electro-Optics*, Vol. 8, pp. 202, 203 and 205 (May 8-13, 1994).
	AK65	Akasaki, I. and Amano, H., "Prospects of GaN-Based Laser Diode," *Japanese Journal of Optics*, Vol. 22, No. 11, pp. 670-675 (November 1993).

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	AE66	Amano, H. and Akasaki, I., "Present and future prospects of GaN-based short-wavelength, light emitting devices," *Oyo Buturi*, Vol. 63, No. 12, pp. 1243-1247 (December 12, 1994).
	AF66	Japanese Article from *Science Forum*, 6 pages (1986).
	AG66	Blakemore, J.S., "Semiconducting and other major properties of gallium arsenide," *Journal of Applied Physics*, Vol. 53, No. 10, American Institute of Physics, pp. R123-R130 and R132-R181 (October 1982).
	AH66	Pramatarova, L.D. *et al.*, "Preparation of GaAs Substrates for MBE," *Cryst. Res. Technol.*, Vol. 23, No. 1, pp. K11 and K13-K15 (1988).
	AI66	Nagata, F. and Kakibayashi, H., "Electron Microscopy for Compound Semiconductors," *J. Electron Microsc.*, Vol. 34, No. 4, pp. 311 and 313-315 (1985).
	AJ66	Gornik, E. and Tsui, D.C., "Voltage-Tunable Far-Infrared Emission from Si Inversion Layers," *Physical Review Letters*, Vol. 37, No. 21, pp. 1425, 1426 and 1428 (November 22, 1976).
	AK66	Holm, D.A. and Taylor, H.F., "Infrared Phase Modulators with Multiple Quantum Wells," *IEEE Journal of Quantum Electronics*, Vol. 25, No. 11, IEEE, pp. 2266 and 2271 (November 1989).

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FORM PTO-1449

SEVENTH SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

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INVENTOR: Yukio SHAKUDA	
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	AC						N/A
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OTHER (Including Author, Title, Date, Pertinent Pages, etc.)

	AE67	Covington, B.C. *et al.*, "Infrared intersubband absorption in GaAs/AlAs multiple quantum wells," *Applied Physics Letters*, Vol. 54, No. 21, American Institute of Physics, pp. 2145 and 2147 (May 22, 1989).
	AF67	Borenstain, S.I. and Katz, J., "Evaluation of the feasibility of a far-infrared laser based on intersubband transitions in GaAs quantum wells," *Applied Physics Letters*, Vol. 55, No. 7, American Institute of Physics, p. 654 (August 14, 1989).
	AG67	Newson, D.J. and Kurobe, A., "Simulation of saturation and relaxation of intersubband absorption in doped quantum wells," *Applied Physics Letters*, Vol. 53, No. 25, American Institute of Physics, pp. 2516 and 2518 (December 19, 1988).
	AH67	Wu, Y., *Metalorganic Molecular Beam Epitaxial Growth and Characterization of ZnSe-Based II-VI Semiconductors*, Dept. of Electrical Engineering, Kyoto University, pp. i-iv, 1-50, 53-140 and 143-159 (May 1991).
	AI67	Page showing graph of BGE v. mole fraction x of InGaAs for light hole, heavy hole, and unstrained structure, 1 page.
	AJ67	Goetz, K.-H. *et al.*, "Optical and crytallographic properties and impurity incorporation of $Ga_xIn_{1-x}As$ ($0.44<x<0.49$) grown by liquid phase epitaxy, vapor phase epitaxy, and metal organic chemical vapor deposition," *Journal of Applied Physics*, Vol. 54, No. 8, American Institute of Physics, pp. 4543-4550 and 4552 (August 1983).
	AK67	Kirby, P.B. *et al.*, "Photoluminescence study of undoped and modulation-doped pseudomorphic $Al_yGa_{1-y}As/In_xGa_{1-x}As/Al_yGa_{1-y}As$ single quantum wells," *Physical Review B*, Vol. 40, No. 5, pp. 3013-3105 and 3018-3020 (August 15, 1989).

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FORM PTO-1449 SEVENTH SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT	ATTY. DOCKET NO. 2005.0020003	APPLICATION NO. 09/604,097
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	AE68	Ekenberg, U., "Enhancement of nonparabolicity efffects in a quantum well," *Physical Review B*, Vol. 36, No. 11, The American Physical Society, pp. 6152 and 6154 (October 15, 1987).
	AF68	Cho, H.-S. and Prucnal P.R., "New formalism of the Kronig-Penney model with application to superlattices," *Physical Review B*, Vol. 36, No. 6, The American Physical Society, pp. 3237, 3238 and 3240 (August 15, 1987).
	AG68	Matsushita Technoresearch Graphical Printouts, 4 pages (April 19, 1994).
	AH68	Kudo, K. *et al.*, "Photoluminescence spectra of undoped GaAs grown by molecular-beam epitaxy at very high and low substrate temperatures," *Journal of Applied Physics*, Vol. 59, No. 3, American Institute of Physics, pp. 888, 889 and 891 (February 1, 1986).
	AI68	Jacob, G. *et al.*, "Gallium Nitride Emitting Devices Preparation and Properties," *Journal of Electronic Materials*, Vol. 7, No. 4, AIME, pp. 499, 501-514 (1978).
	AJ68	Butler, J.K., "Theory of Transverse Cavity Mode Selection in Homojunction and Heterojunction Semiconductor Diode Lasers," Page 81, Reprinted from *Journal of Applied Physics*, Vol. 42, pp. 4447-4457 (October 1971).
	AK68	Hamada, H. *et al.*, "Wide-Stripe AlGaInP Laser Diode Current-Blocking Region Near Facets Grown on Misoriented Substrates," *Electronics Letters*, Vol. 27, No. 19, pp. 1713-1715 (September 12, 1991).

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	AE69	Xu, Y.-N. and Ching, W.Y., "Electronic, optical, and structural properties of some wurtzite crystals," *Physical Review B*, Vol. 48, No. 7, The American Physical Society, pp. 4335-4348 (August 15, 1993).
	AF69	Mohammad, S.N. *et al.*, "Emerging Gallium Nitride Based Devices," *Proceedings of the IEEE*, Vol. 83, No. 10, pp. 1320-1355 (October 1995).
	AG69	Masu, K. *et al.*, "Transmission Electron Microscopic Observation of AlN/α-Al_2O_3 Heteroepitaxial Interface with Initial-Nitriding AlN Layer," *Japanese Journal of Applied Physics*, Vol. 34, Part 2, No. 6B, pp. L760, L761 and L763 (June 15, 1995).
	AH69	Nahamura, S. *et al.*, "Cd-Doped InGaN Films Grown on GaN Films," *Japanese Journal of Applied Physics*, Vol. 32, Part 2, No. 3A, pp. L338 and L340 (March 1, 1993).
	AI69	Wong, W.S. *et al.*, "Fabrication of $In_xGa_{1-x}N$ Laser Diodes on Copper Substrates by Laser Lift," 2 pages.
	AJ69	Morkoç, H. *et al.*, "GaN based II-V nitrides by molecular beam epitaxy," *Journal of Crystal Growth*, Vol. 150, Elsevier Science B.V., pp. 887-890 (1995).
	AK69	Pearton, S.J., "Hydrogenation of III-V Semiconductors During Processing," *Materials Science Forum*, Vols. 148-149, Trans Tech Publications, Switzerland, pp. 113-134, 138 and 139 (1994).

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	AE70	Stockman, S.A. and Stillman, G.E., "Hydrogen in III-V Device Structures," *Materials Science Forum*, Vols. 148-149, Trans Tech Publications, Switzerland, pp. 501-524, 529-531, 534 and 535 (1994).
	AF70	Bykhovski, A. *et al.*, "Strain and charge distribution in GaN-AlN-GaN semiconductor-insulator-semiconductor structure for arbitrary growth orientation," *Applied Physics Letters*, Vol. 63, No. 16, American Institute of Physics, pp. 2243 and 2245 (October 18, 1993).
	AG70	Wickenden, D.K. *et al.*, "High quality self-nucleated $Al_xGa_{1-x}N$ layers on (00.1) sapphire by low-pressure metalorganic chemical vapor deposition," *Applied Physics Letters*, Vol. 65, No. 16, American Institute of Physics, pp. 2024 and 2026 (October 17, 1994).
	AH70	
	AI70	
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